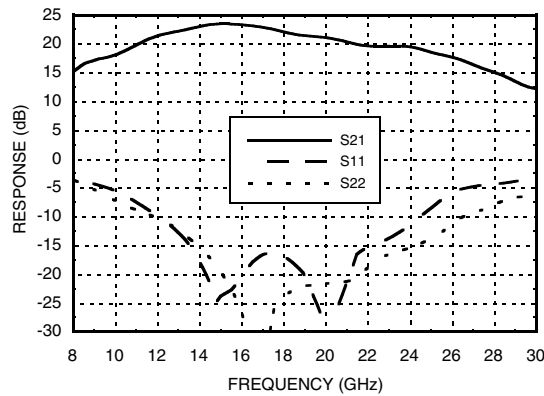


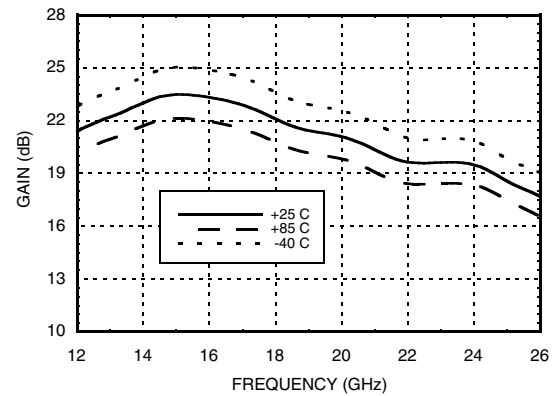


**GaAs PHEMT MMIC LOW NOISE  
AMPLIFIER, 13 - 25 GHz**

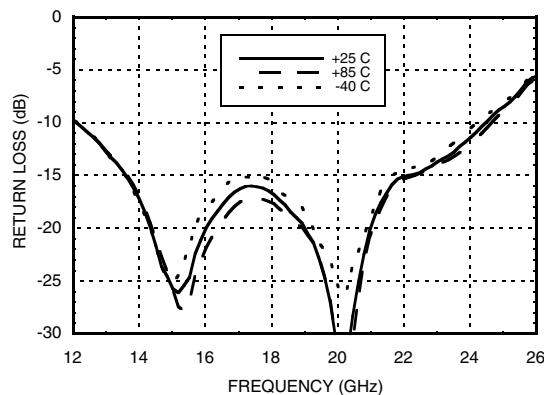
**Broadband Gain & Return Loss**



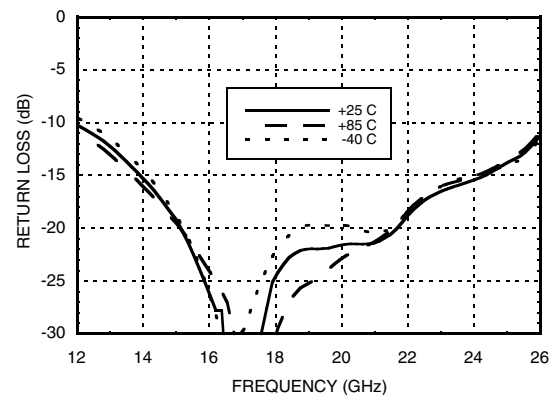
**Gain vs. Temperature**



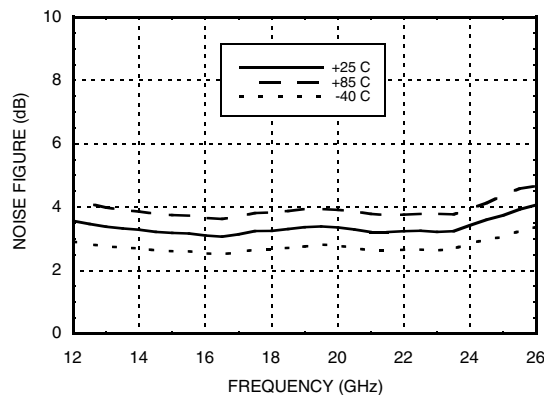
**Input Return Loss vs. Temperature**



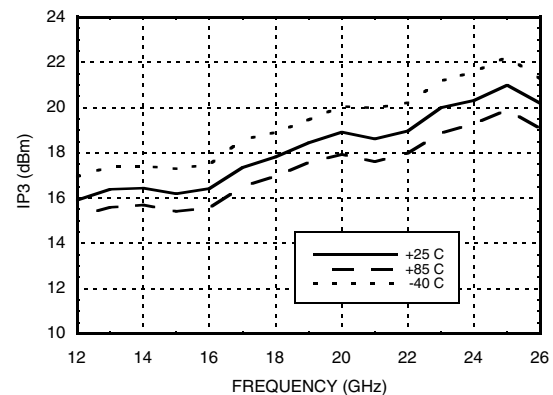
**Output Return Loss vs. Temperature**



**Noise Figure vs. Temperature**



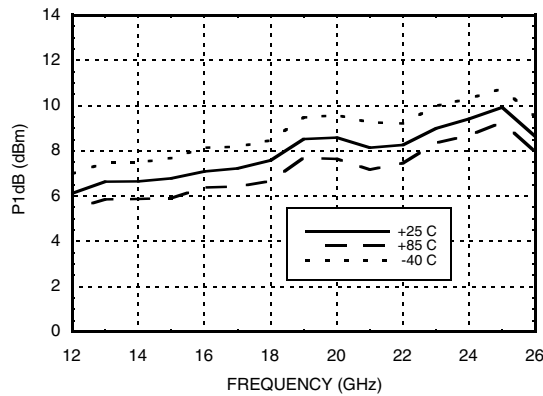
**Output IP3 vs. Temperature**



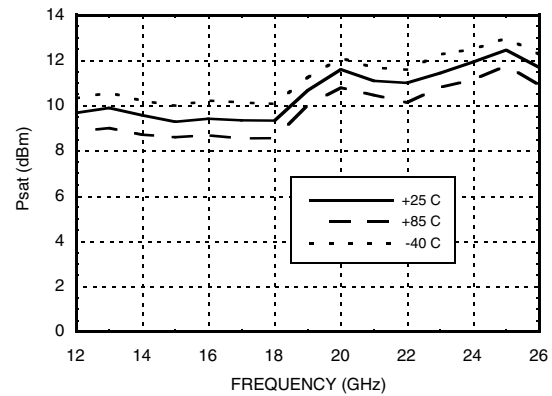


**GaAs PHEMT MMIC LOW NOISE  
AMPLIFIER, 13 - 25 GHz**

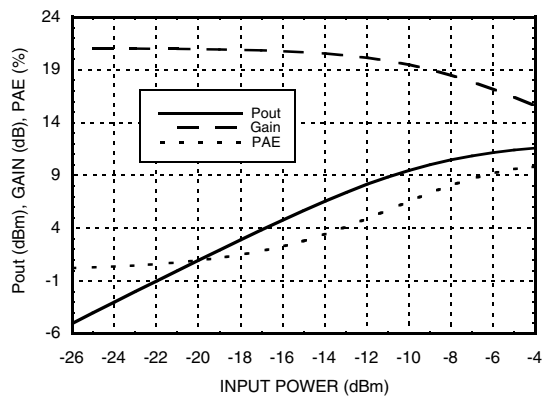
**P1dB vs. Temperature**



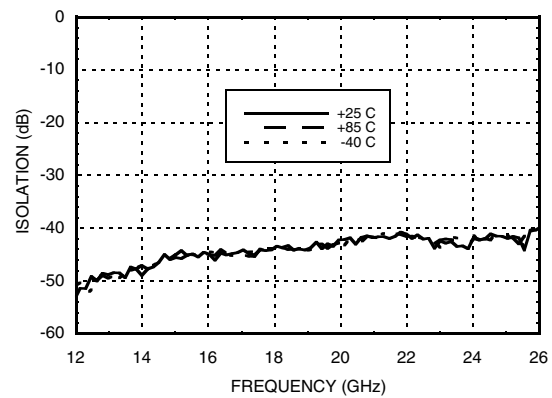
**Psat vs. Temperature**



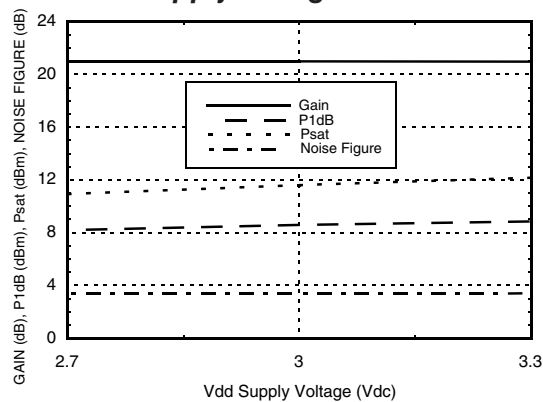
**Power Compression @ 20 GHz**



**Reverse Isolation vs. Temperature**



**Gain, Power & Noise Figure  
vs. Supply Voltage @ 20 GHz**





## GaAs PHEMT MMIC LOW NOISE AMPLIFIER, 13 - 25 GHz

### Absolute Maximum Ratings

|  |                |
|--|----------------|
| Drain Bias Voltage (Vdd)   | +5.5 Vdc       |
| RF Input Power (RFIN)(Vdd = +3.0 Vdc)                                      | 0 dBm          |
| Channel Temperature  | 175 °C         |
| Continuous P <sub>diss</sub> (T= 85 °C)<br>(derate 3.62 mW/°C above 85 °C) | 0.326 W        |
| Thermal Resistance<br>(channel to ground paddle)                           | 276 °C/W       |
| Storage Temperature  | -65 to +150 °C |
| Operating Temperature  | -40 to +85 °C  |

### Typical Supply Current vs. Vdd

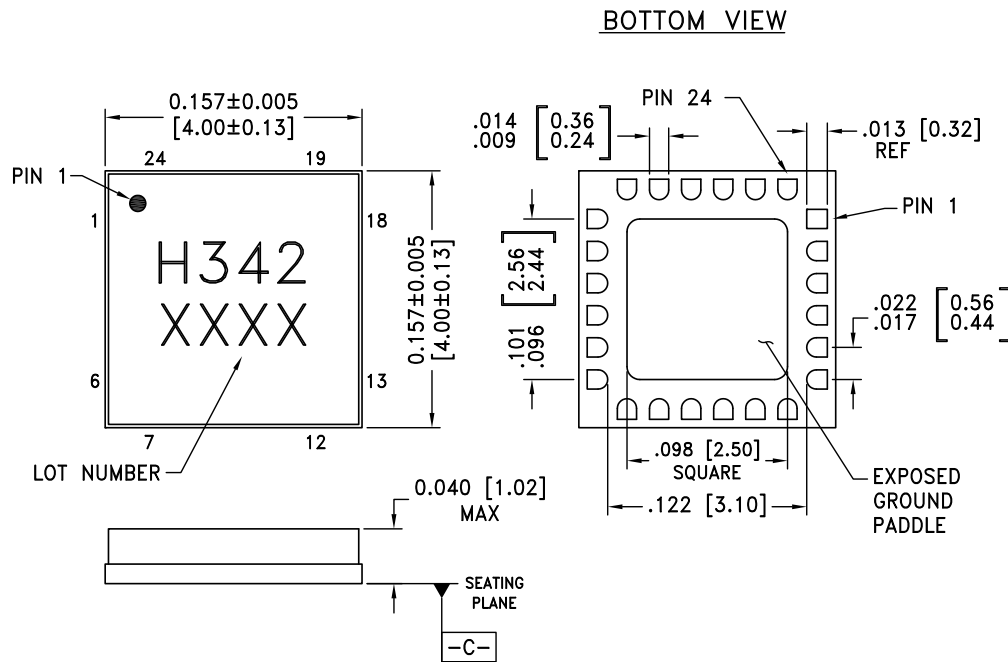
| Vdd (Vdc) | I <sub>dd</sub> (mA) |
|-----------|----------------------|
| +2.7      | 42                   |
| +3.0      | 43                   |
| +3.3      | 44                   |

Note: Amplifier will operate over full voltage ranges shown above.



ELECTROSTATIC SENSITIVE DEVICE  
OBSERVE HANDLING PRECAUTIONS

### Outline Drawing



#### NOTES:

1. PACKAGE BODY MATERIAL: ALUMINA.
2. LEAD AND GROUND PADDLE PLATING: GOLD FLASH OVER NICKEL.
3. DIMENSIONS ARE IN INCHES (MILLIMETERS).
4. LEAD SPACING TOLERANCE IS NON-CUMULATIVE.
5. PACKAGE WARP SHALL NOT EXCEED 0.05MM DATUM  $\overline{C}$ .
6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.

### Package Information

| Part Number | Package Body Material | Lead Finish      | MSL Rating          | Package Marking <sup>[2]</sup> |
|-------------|-----------------------|------------------|---------------------|--------------------------------|
| HMC342LC4   | Alumina, White        | Gold over Nickel | MSL3 <sup>[1]</sup> | H342<br>XXXX                   |

[1] Max peak reflow temperature of 260 °C

[2] 4-Digit lot number XXXX


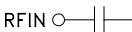
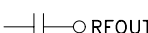
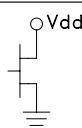
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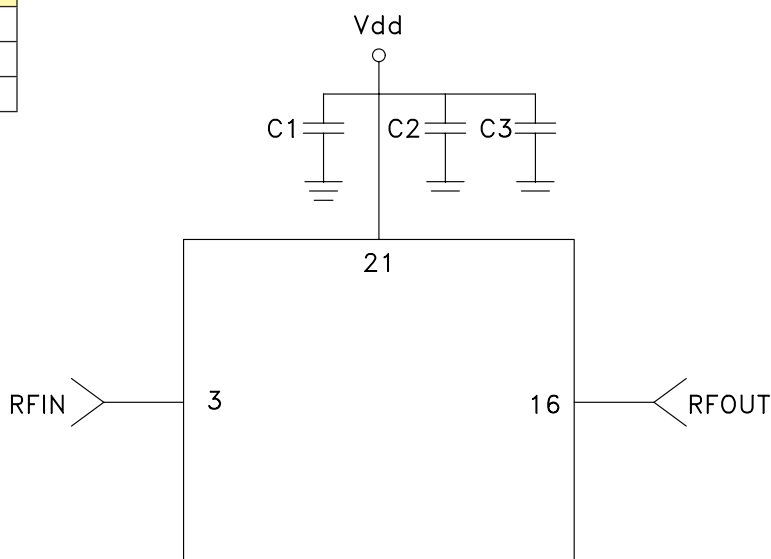
## GaAs PHEMT MMIC LOW NOISE AMPLIFIER, 13 - 25 GHz

### Pin Descriptions

| Pin Number                     | Function | Description  | Interface Schematic   |
|--------------------------------|----------|--|---|
| 1, 5 - 14,<br>18 - 20, 22 - 24 | N/C      | No connection required. These pins may be connected to RF/DC ground without affecting performance.             |   |
| 2, 4, 15, 17                   | GND      | Package base has an exposed metal ground that must also be connected to RF/DC ground.                          |  |
| 3                              | RFIN     | This pin is AC coupled and matched to 50 Ohms.   |  |
| 16                             | RFOUT    | This pin is AC coupled and matched to 50 Ohms.   |  |
| 21                             | Vdd      | Power Supply Voltage for the amplifier. External bypass capacitors of 100 pF, 1000pF, and 2.2 μF are required. |  |

### Application Circuit

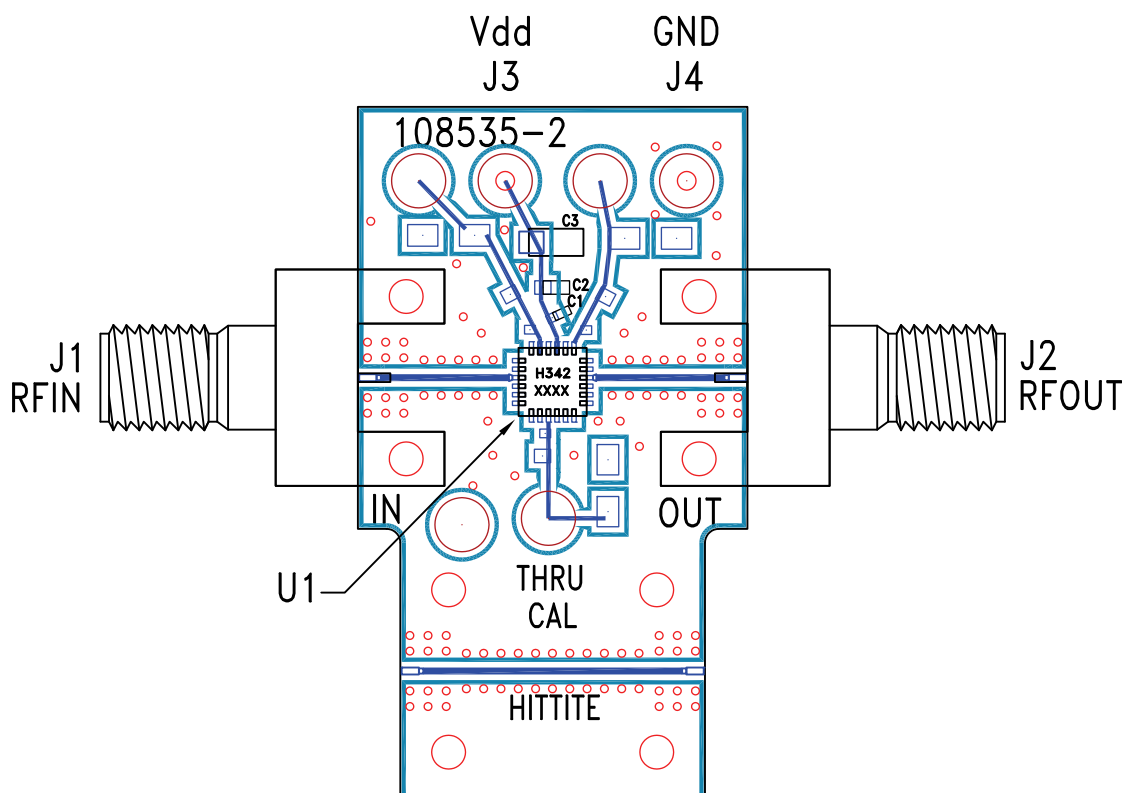
| Component | Value    |
|-----------|----------|
| C1        | 100 pF   |
| C2        | 1,000 pF |
| C3        | 2.2 μF   |





## GaAs PHEMT MMIC LOW NOISE AMPLIFIER, 13 - 25 GHz

### Evaluation PCB



### List of Materials for Evaluation PCB 110209 <sup>[1]</sup>

| Item               | Description                    |
|--------------------|--------------------------------|
| J1, J2             | 2.92 mm PC mount K-connector   |
| J3, J4             | DC Pin                         |
| C1                 | 100 pF capacitor, 0402 Pkg..   |
| C2                 | 1,000 pF Capacitor, 0603 Pkg.. |
| C3                 | 2.2µF Capacitor, Tantalum      |
| U1                 | HMC342LC4 Amplifier            |
| PCB <sup>[2]</sup> | 108535 Evaluation PCB          |

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350.

The circuit board used in this application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.